

Notice of Allowability	Application No.	Applicant(s)	
	10/065,920	VOLLERTSEN, ROLF-P.	
	Examiner	Art Unit	
	Anjan K Deb	2858	
The MAILING DATE of this communication appearance of the second allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIOF of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication IGHTS. This application is subject to	olication. If not include will be mailed in due	ed course. THIS
1. \boxtimes This communication is responsive to <u>amendment filed 03/2</u>	<u>24/2004</u> .		
2. The allowed claim(s) is/are <u>1-38</u> .			
3. \boxtimes The drawings filed on <u>29 November 2002</u> are accepted by	the Examiner.		
4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv 6. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner' Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the deposit of the paper No./Mail Date attached Examiner's comment regarding REQUIREMENT	e been received. e been received in Application No cuments have been received in this of this communication to file a reply MENT of this application. hitted. Note the attached EXAMINER es reason(s) why the oath or declara st be submitted. son's Patent Drawing Review (PTO d's Amendment / Comment or in the Coll. 1.84(c)) should be written on the drawing the header according to 37 CFR 1.121(c) esit of BIOLOGICAL MATERIAL re	national stage applical complying with the reconstruction is deficient. 948) attached office action of the dol. must be submitted.	quirements NOTICE OF
Attachm nt(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	Paper No./Mail Da	(PTO-413), te ment/Comment	owance

DETAILED ACTION

1. This office action is in response to amendment filed 03/24/2004.

Allowable Subject Matter

2. Claims 1-38 are allowed.

Reasons for Allowance

3. The following is an examiner's statement of reasons for allowance:

The primary reason for allowance of the claims is the inclusion of determining a critical breakdown resistance of the test structure, and recording a critical breakdown time when the operating resistance of the test structure is equal to or smaller than the critical breakdown resistance.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Pertinent Art

 The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Satake, H.; Toriumi, A.; (Dielectric breakdown mechanism of thin-SiO₂ studied by the post-breakdown resistance statistics. Electron Devices, IEEE Transactions on, Volume: 47, Issue: 4, April 2000 Pages:741 – 745) discloses performing reliability studies on thin film dielectric breakdown of gate oxides by measuring resistance to breakdown R_{bd} of dielectric, wherein R_{bd} is defined as 0.5 Vg/I_{bd} where Vg is gate voltage and I_{bd} gate current after breakdown. Satake et al. does not disclose recording a critical breakdown time when the operating resistance of the test structure is equal to or smaller than the critical breakdown resistance.

Takeda, K.-I.; Hinode, K.; Oodake, I.; Oohashi, N.; Yamaguchi, H.; (Enhanced dielectric breakdown lifetime of the copper/silicon nitride/silicon dioxide structure. Reliability Physics Symposium Proceedings, 1998. 36th Annual. 1998 IEEE International, 31 March-2 April 1998 Pages:36 – 41) discloses determining time to beakdown τ_{bd} of a dielectric structure (Fig. 1) as a function of electric field strength E_{av} (Fig. 6). Takeda et al. does not disclose recording a critical breakdown time when the operating resistance of the test structure is equal to or smaller than the critical breakdown resistance.

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Contact Information

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Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Dr. Anjan K. Deb whose telephone number is (571)-272-2228. If

attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, N. Le,

can be reached at (571)272-2233.

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5/24/04